《风光欣》技术资料

KSP13/14

NPN EPITAXIAL SILICON TRANSISTOR

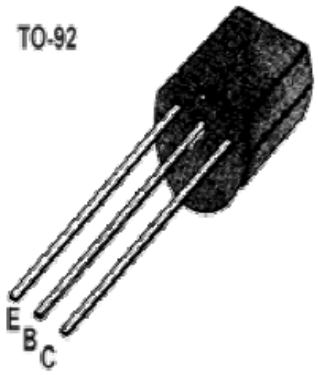
DARINGTON TRANSISTOR

*Collector-Emitter Voltage:V_{CES}=30V

*Collector Dissipation:Pc(max)=625mW

ABSOLUTE MAXIMUM RATINGS(TA=25 ℃)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CES}	30	V
Emitter -Base Voltage	V_{EBO}	10	V
Collector Current	Ic	500	mA
Collector Dissipation	Pc	625	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55 ~150	℃



ELECTRCAL CHARACTERISTICS(TA=25 ℃)

Characteristic		Symbol	Test Conditions	Min	Max	Unit
Collector- Emitter Breakdown Voltage		BV_{CES}	Ic= 100μA,I_B= 0	30		V
Collector-Cut-off Current		I_{CBO}	V_{CB}= 30V,I_E=0		100	nA
Emitter-Cut-off Current		I_{EBO}	V_{BE}= 10V,Ic= 0		100	nA
DC Current Gain	:KSP13	h_{FE}	V_{CE}= 5V,Ic= 10mA	5, 000		
	:KSP14		V_{CE}= 5V,Ic= 10mA	10, 000		
	:KSP13	h_{FE}	V_{CE}= 5V,Ic= 100mA	10, 000		
	:KSP14		V_{CE}= 5V,Ic= 100mA	20, 000		
Collector- Emitter Saturation Voltage		$V_{CE(sat)}$	Ic= 100mA,I_B= 0.1mA		1. 5	V
Basa- Emitter On Voltage		$V_{BE(on)}$	V_{CE}= 5V,Ic= 100mA		2. 0	V
Current Gain Bandwidth Product		f_T	VCE = 5V,Ic=10mA,F=100M	125		MHZ